TOSHIBA TLN117

#### TOSHIBA INFRARED LED GaAs INFRARED EMITTER

# **TLN117**

OPTO-ELECTRONIC SWITCH FLOPPY DISK DRIVE OPTICAL MOUSE OPTICAL TOUCH SENSOR

• Small side view epoxy resin package

• High radiant intensity:  $I_E = 0.8 \text{mW/sr}$  (MIN.) at  $I_F = 20 \text{mA}$ 

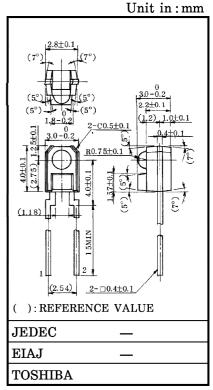
• Half value angle :  $\theta_{\frac{1}{2}} = \pm 15^{\circ}$  (TYP.)

• Optimum in combination with the following photo detectors which have identical external dimensions.

Photo Transistor	TPS621, TPS622
Photo Dairilngton Transistor	TPS625, TPS626

## MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Forward Current	$I_{\mathbf{F}}$	50	mA
Pulse Forward Current	$I_{\mathrm{FP}}$	600 (Note 1)	mA
Forward Current Derating (Ta>25°C)	$\Delta I_{\mathbf{F}} / {^{\circ}\mathbf{C}}$	-0.33	mA/°C
Reverse Voltage	$V_{\mathbf{R}}$	5	$\mathbf{v}$
Operating Temperature Range	$T_{\mathrm{opr}}$	-25~85	$^{\circ}\mathrm{C}$
Storage Temperature Range	$\mathrm{T_{stg}}$	-40~100	°C
Soldering Temperature (5s)	$T_{sol}$	260 (Note 2)	°C



Weight: 0.1g (TYP.)

#### PIN CONNECTION

 $1 \circ 4 \circ 2 \circ 1$ . CATHODE 2. ANODE

Note 1. Pulse Width $\leq 100 \mu s$ , Repetitive Frequency=100Hz

2. Soldering portion of lead: above 2mm from the body of the device.

## OPTO-ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Forward Voltage	$V_{\mathbf{F}}$	I <sub>F</sub> =10mA		1.0	1.15	1.30	V
Reverse Current	$I_{ m R}$	$V_R = 5V$		_	_	10	$\mu \mathbf{A}$
Radiant Intensity	${ m I_{ m E}}$	$I_{ m F}\!=\!20{ m mA}$	TLN117	0.8	_		mW/sr
			TLN117 (A)	0.8	_	3	
			TLN117 (B)	2	_	7.5	
			TLN117 (C)	5	_	18.7	
Radiant Power	PO	$I_{\mathbf{F}} = 20 \text{mA}$		_	2.5	_	mW
Peak Emission Wavelength	$\lambda_{\mathbf{P}}$	$I_{ m F}\!=\!20{ m mA}$		_	940	_	nm
Spectral Line Half Width	Δλ	$I_{ m F} = 20 { m mA}$		_	50	_	nm
Half Value Angle	$\theta_{\frac{1}{2}}$	$I_{ m F}\!=\!20{ m mA}$		_	±15	_	0

#### 961001EAC2

TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

**TOSHIBA TLN117** 

### **PRECAUTION**

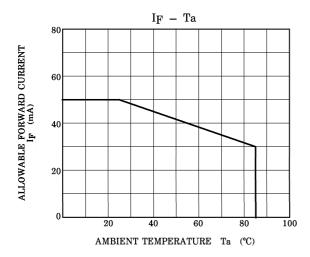
Please be careful of the followings.

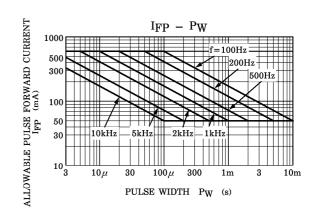
When the lead is formed, the lead shall be formed at a distance of 2mm from the body without leaving forming stress to the body of the device. Soldering shall be performed after lead forming.

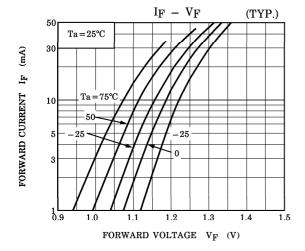
961001EAC2

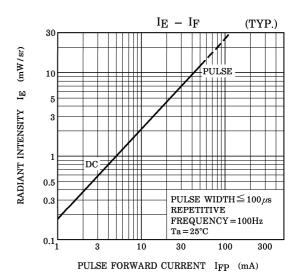
Gallium arsenide (GaAs) is a substance used in the products described in this document. GaAs dust and fumes are toxic. Do not break, cut or pulverize the product, or use chemicals to dissolve them. When disposing of the products, follow the appropriate regulations. Do not dispose of the products with other industrial waste or with domestic garbage.

The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.

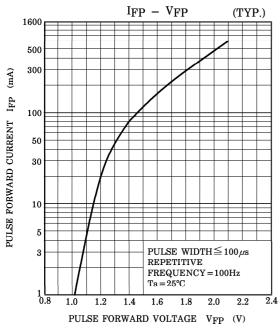


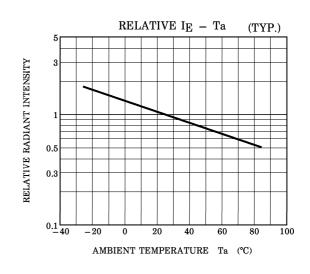


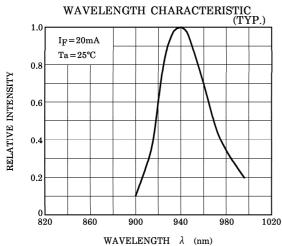


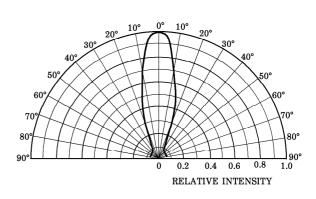


TOSHIBA TLN117









RADIATION PATTERN

(TYP.)

 $(Ta = 25^{\circ}C)$